

Karen J Kirkby

List of Publications by Year in descending order

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179
papers

3,581
citations

172207

29
h-index

174990

52
g-index

181
all docs

181
docs citations

181
times ranked

2801
citing authors

#	ARTICLE	IF	CITATIONS
1	A silicon/iron-disilicide light-emitting diode operating at a wavelength of 1.5 μm . <i>Nature</i> , 1997, 387, 686-688.	13.7	727
2	Optical absorption study of ion beam synthesized polycrystalline semiconducting FeSi ₂ . <i>Journal of Applied Physics</i> , 1995, 78, 1958-1963.	1.1	213
3	Biological effectiveness on live cells of laser driven protons at dose rates exceeding 109 Gy/s. <i>AIP Advances</i> , 2012, 2, .	0.6	97
4	On the origin of the 1.5 μm luminescence in ion beam synthesized FeSi_2 . <i>Applied Physics Letters</i> , 1996, 68, 1649-1650.	1.5	89
5	Improved subthreshold characteristics of n-channel SOI transistors. <i>IEEE Electron Device Letters</i> , 1986, 7, 570-572.	2.2	81
6	Evaluation of poly (ADP-ribose) polymerase inhibitor ABT-888 combined with radiotherapy and temozolomide in glioblastoma. <i>Radiation Oncology</i> , 2013, 8, 65.	1.2	81
7	An endogenous nanomineral chaperones luminal antigen and peptidoglycan to intestinal immune cells. <i>Nature Nanotechnology</i> , 2015, 10, 361-369.	15.6	73
8	Investigation of gold nanoparticle radiosensitization mechanisms using a free radical scavenger and protons of different energies. <i>Physics in Medicine and Biology</i> , 2014, 59, 6431-6443.	1.6	69
9	Ion beam synthesis of thin buried layers of SiO ₂ in silicon. <i>Vacuum</i> , 1986, 36, 877-881.	1.6	62
10	Mechanism of buried FeSi_2 -SiC formation by implanted carbon in silicon. <i>Thin Solid Films</i> , 1990, 191, 147-164.	0.8	53
11	Optical properties and phase transformations in FeSi and FeSi_2 iron disilicide layers. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1994, 84, 168-171.	0.6	51
12	Electroluminescence of FeSi_2 -Light Emitting Devices. <i>Japanese Journal of Applied Physics</i> , 2001, 40, 4041-4044.	0.8	42
13	Investigation of the luminescence properties of Si/ FeSi_2 /Si heterojunction structures fabricated by ion beam synthesis. <i>Journal of Luminescence</i> , 1993, 57, 25-27.	1.5	40
14	Modelling direct DNA damage for gold nanoparticle enhanced proton therapy. <i>Nanoscale</i> , 2017, 9, 18413-18422.	2.8	39
15	Formation of buried layers of FeSi_2 -SiC using ion beam synthesis and incoherent lamp annealing. <i>Applied Physics Letters</i> , 1987, 51, 2242-2244.	1.5	37
16	Determination of the Deposition Order of Overlapping Latent Fingerprints and Inks Using Secondary Ion Mass Spectrometry. <i>Analytical Chemistry</i> , 2012, 84, 4083-4087.	3.2	37
17	Measuring and modelling cell-to-cell variation in uptake of gold nanoparticles. <i>Analyst</i> , 2013, 138, 7070.	1.7	37
18	Chemical changes exhibited by latent fingerprints after exposure to vacuum conditions. <i>Forensic Science International</i> , 2013, 230, 81-86.	1.3	36

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19	Geometrical structures for radiation biology research as implemented in the TOPAS-nBio toolkit. <i>Physics in Medicine and Biology</i> , 2018, 63, 175018.	1.6	36
20	Deactivation of ultrashallow boron implants in preamorphized silicon after nonmelt laser annealing with multiple scans. <i>Applied Physics Letters</i> , 2006, 89, 192105.	1.5	35
21	EPR of defects in silicon-on-insulator structures formed by ion implantation. I. O ⁺ implantation. <i>Journal of Physics C: Solid State Physics</i> , 1986, 19, 6417-6432.	1.5	34
22	Novel dielectric/silicon planar structures formed by ion beam synthesis. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1987, 21, 129-133.	0.6	33
23	Ion beam synthesis of $\hat{1}\pm$ and $\hat{1}^2$ FeSi ₂ layers. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1993, 74, 60-64.	0.6	32
24	<i>In Vitro</i> Evaluation of Combined Temozolomide and Radiotherapy Using X-rays and High-Linear Energy Transfer Radiation for Glioblastoma. <i>Radiation Research</i> , 2012, 177, 651-662.	0.7	32
25	A scanning focussed vertical ion nanobeam: A new UK facility for cell irradiation and analysis. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2007, 260, 97-100.	0.6	31
26	Electrical, optical and materials properties of ion beam synthesised (IBS) FeSi ₂ . <i>Nuclear Instruments & Methods in Physics Research B</i> , 1995, 106, 364-371.	0.6	30
27	Is there a future for semiconducting silicides? (invited). <i>Microelectronic Engineering</i> , 2000, 50, 223-235.	1.1	30
28	Integrated Ion Beam Analysis (IBA) in Gunshot Residue (GSR) characterisation. <i>Forensic Science International</i> , 2013, 231, 219-228.	1.3	30
29	Buried layers of silicon oxy-nitride fabricated using ion beam synthesis. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1988, 32, 427-432.	0.6	29
30	Trace element profiling of gunshot residues by PIXE and SEM-EDS: a feasibility study. <i>X-Ray Spectrometry</i> , 2009, 38, 190-194.	0.9	29
31	Dislocation formation related with high oxygen dose implantation on silicon. <i>Journal of Applied Physics</i> , 1991, 69, 793-802.	1.1	28
32	A transmission electron microscope investigation of the dose dependence of the microstructure of silicon-on-insulator structures formed by nitrogen implantation of silicon. <i>Journal of Applied Physics</i> , 1991, 69, 3503-3511.	1.1	28
33	Scintillator-based ion beam profiler for diagnosing laser-accelerated ion beams. <i>Proceedings of SPIE</i> , 2011, . .	0.8	28
34	A new quantitative method for gunshot residue analysis by ion beam analysis. <i>Analyst, The</i> , 2013, 138, 4649.	1.7	27
35	Monitoring of SIMOX layer properties and implantation temperature by optical measurements. <i>Semiconductor Science and Technology</i> , 1987, 2, 687-690.	1.0	26
36	Radiosensitization of glioblastoma cells using a histone deacetylase inhibitor (SAHA) comparing carbon ions with X-rays. <i>International Journal of Radiation Biology</i> , 2015, 91, 90-98.	1.0	26

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37	Isoelectronic bound exciton photoluminescence from a metastable defect in sulphur-doped silicon. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1989, 4, 303-307.	1.7	25
38	A Focused Scanning Vertical Beam for Charged Particle Irradiation of Living Cells with Single Counted Particles. <i>Radiation Research</i> , 2012, 178, 182-190.	0.7	25
39	Clinically relevant nanodosimetric simulation of DNA damage complexity from photons and protons. <i>RSC Advances</i> , 2019, 9, 6845-6858.	1.7	25
40	Proton beam therapy: perspectives on the National Health Service England clinical service and research programme. <i>British Journal of Radiology</i> , 2020, 93, 20190873.	1.0	25
41	SIMS analysis of buried silicon nitride layers formed by high dose implantation of ^{14}N and ^{15}N . <i>Nuclear Instruments & Methods in Physics Research B</i> , 1986, 15, 214-217.	0.6	24
42	High-performance SOI-CMOS Transistors in oxygen-implanted silicon without epitaxy. <i>IEEE Electron Device Letters</i> , 1987, 8, 291-293.	2.2	24
43	The formation of compound layers in silicon by ion beam synthesis. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1990, 50, 368-378.	0.6	24
44	Preclinical dosimetry: exploring the use of small animal phantoms. <i>Radiation Oncology</i> , 2019, 14, 134.	1.2	24
45	Determining the parameter space for effective oxygen depletion for FLASH radiation therapy. <i>Physics in Medicine and Biology</i> , 2021, 66, 055020.	1.6	24
46	Electrical activation of solid-phase epitaxially regrown ultra-low energy boron implants in Ge preamorphised silicon and SOI. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2005, 237, 107-112.	0.6	22
47	Current status of cranial stereotactic radiosurgery in the UK. <i>British Journal of Radiology</i> , 2016, 89, 20150452.	1.0	22
48	Diffusion and activation of ultrashallow B implants in silicon on insulator: End-of-range defect dissolution and the buried $\text{Si}^{\bullet}\text{-SiO}_2$ interface. <i>Applied Physics Letters</i> , 2006, 89, 042111.	1.5	20
49	Insights into the non-homologous end joining pathway and double strand break end mobility provided by mechanistic in silico modelling. <i>DNA Repair</i> , 2020, 85, 102743.	1.3	20
50	The Effects of Dose and Target Temperature on Low Energy SIMOX Layers. <i>Journal of the Electrochemical Society</i> , 1993, 140, 1780-1786.	1.3	19
51	FLASH radiotherapy: Considerations for multibeam and hypofractionation dose delivery. <i>Radiotherapy and Oncology</i> , 2021, 164, 122-127.	0.3	19
52	Order domain boundaries in ion beam synthesized semiconducting FeSi_2 layers. <i>Applied Physics Letters</i> , 1995, 67, 667-669.	1.5	18
53	Correlation of local structure and electrical activation in arsenic ultrashallow junctions in silicon. <i>Journal of Applied Physics</i> , 2008, 104, .	1.1	18
54	A survey of two-stage focusing systems for nanobeam design. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2007, 260, 8-14.	0.6	17

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55	Heavy charged particle beam therapy and related new radiotherapy technologies: The clinical potential, physics and technical developments required to deliver benefit for patients with cancer. British Journal of Radiology, 2020, 93, 20200247.	1.0	16
56	Measurement and modeling of circuit speed of CMOS on oxygen-implanted SOI. IEEE Transactions on Electron Devices, 1987, 34, 1713-1718.	1.6	15
57	The evolution of the Si/SiO ₂ interface in buried oxide layers formed by high dose oxygen implantation into silicon. Nuclear Instruments & Methods in Physics Research B, 1987, 19-20, 290-293.	0.6	15
58	Ion beam synthesized silicides: growth, characterization and devices. Thin Solid Films, 2001, 381, 188-193.	0.8	15
59	Maskless proton beam writing in gallium arsenide. Nuclear Instruments & Methods in Physics Research B, 2007, 260, 437-441.	0.6	15
60	A mathematical model of response of cells to radiation. Nuclear Instruments & Methods in Physics Research B, 2007, 255, 18-22.	0.6	15
61	Dielectrically isolated silicon- ϵ on- ϵ insulator islands by masked oxygen implantation. Applied Physics Letters, 1987, 51, 1419-1421.	1.5	14
62	Resistivity of ion beam synthesised CoSi ₂ . Electronics Letters, 1989, 25, 1532.	0.5	14
63	Determination of crystallite propagation in laser annealed amorphous silicon by normal incidence spectral reflectance. Applied Physics Letters, 1996, 69, 1623-1625.	1.5	14
64	Boron deactivation in preamorphized silicon on insulator: Efficiency of the buried oxide as an interstitial sink. Applied Physics Letters, 2007, 91, .	1.5	14
65	Design concept for a novel SQUID-based microdosimeter. Radiation Protection Dosimetry, 2011, 143, 427-431.	0.4	14
66	An open source heterogeneous 3D printed mouse phantom utilising a novel bone representative thermoplastic. Physics in Medicine and Biology, 2020, 65, 10NT02.	1.6	14
67	Modelling of ¹⁸ O tracer studies of the oxygen redistribution during formation of SiO ₂ layers by high dose implantation. Thin Solid Films, 1988, 161, 333-342.	0.8	13
68	Photoluminescence studies of silicon- ϵ on- ϵ insulator substrates formed by oxygen implantation. Applied Physics Letters, 1988, 52, 465-467.	1.5	13
69	Identification of CoSi inclusions within buried CoSi ₂ layers formed by ion implantation. Journal of Applied Physics, 1990, 68, 3792-3794.	1.1	13
70	New developments in the applications of proton beam writing. Nuclear Instruments & Methods in Physics Research B, 2005, 237, 188-192.	0.6	13
71	Characterisation of inhomogeneous inclusions in Darwin glass using ion beam analysis. Nuclear Instruments & Methods in Physics Research B, 2009, 267, 2219-2224.	0.6	13
72	â€œBroadbeamâ€•irradiation of mammalian cells using a vertical microbeam facility. Radiation and Environmental Biophysics, 2013, 52, 513-521.	0.6	13

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73	Assessing localized dosimetric effects due to unplanned gas cavities during pelvic MR-guided radiotherapy using Monte Carlo simulations. <i>Medical Physics</i> , 2019, 46, 5807-5815.	1.6	13
74	Formation mechanism and structures of buried oxy-nitride layers produced by ion beam synthesis. <i>Vacuum</i> , 1986, 36, 891-895.	1.6	12
75	Improved quality Si ₃ N ₄ structures by ion beam synthesis and lamp annealing. <i>Applied Physics Letters</i> , 1987, 50, 1882-1884.	1.5	12
76	Optical and compositional studies of buried oxide layers in silicon formed by high dose implantation. <i>Applied Surface Science</i> , 1987, 30, 390-396.	3.1	12
77	Study of the microstructure of low energy (70 keV) oxygen implanted silicon. <i>Applied Physics Letters</i> , 1991, 59, 3130-3132.	1.5	12
78	Microstructural studies of epitaxial CoSi ₂ layers on silicon produced by ion beam synthesis and rapid thermal annealing. <i>Journal of Applied Physics</i> , 1993, 74, 7129-7133.	1.1	12
79	Characterisation of the University of Surrey Ion Beam Centre in-air scanning microbeam. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2005, 231, 26-31.	0.6	12
80	The use of microbeams to investigate radiation damage in living cells. <i>Applied Radiation and Isotopes</i> , 2009, 67, 436-439.	0.7	12
81	Mass-dispersive recoil spectrometry studies of oxygen and nitrogen redistribution in ion-beam-synthesized buried oxynitride layers in silicon. <i>Applied Physics Letters</i> , 1988, 52, 1871-1873.	1.5	11
82	Dose dependence of crystallinity and resistivity in ion beam synthesised CoSi ₂ layers. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1991, 55, 836-841.	0.6	11
83	Structural properties of ion beam synthesized iron - cobalt silicide. <i>Journal Physics D: Applied Physics</i> , 1996, 29, 1822-1830.	1.3	11
84	New developments on the Surrey microbeam applications to lithography. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2005, 231, 428-432.	0.6	11
85	RBS/EBS/PIXE measurement of single-walled carbon nanotube modification by nitric acid purification treatment. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2008, 266, 1569-1573.	0.6	11
86	Microstructure of silicon-on-insulator structures produced by high dose nitrogen implantation of silicon. <i>Vacuum</i> , 1986, 36, 925-928.	1.6	10
87	Optimisation of SIMOX structures formed by ion beam synthesis. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1989, 37-38, 290-295.	0.6	10
88	PIXE analysis to determine the trace-element concentrations in a series of galena (PbS) specimens from different localities. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1990, 45, 327-332.	0.6	10
89	Ion beam synthesis of epitaxial CoSi ₂ layers and the redistribution of dopants within them. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1992, 68, 369-379.	0.6	10
90	Waveguiding in epitaxial 3C-silicon carbide on silicon. <i>Electronics Letters</i> , 1995, 31, 1438-1439.	0.5	10

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91	A computer model of the Bystander effect: Effects of individual behaviours on the population response. <i>Applied Radiation and Isotopes</i> , 2009, 67, 440-442.	0.7	10
92	Microbeam PIXE analysis of platinum resistant and sensitive ovarian cancer cells. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2010, 268, 2168-2171.	0.6	10
93	Multi-institutional dosimetric delivery assessment of intracranial stereotactic radiosurgery on different treatment platforms. <i>Radiotherapy and Oncology</i> , 2020, 147, 153-161.	0.3	10
94	Formation of multilayer Si ₃ N ₄ structures by nitrogen ion implantation. <i>Electronics Letters</i> , 1986, 22, 467.	0.5	9
95	TEM investigation of ion beam synthesized semiconducting FeSi ₂ . <i>Materials Letters</i> , 1995, 23, 215-220.	1.3	9
96	Proton beam lithography at the University of Surrey's Ion Beam Centre. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2006, 242, 387-389.	0.6	9
97	Uphill diffusion of ultralow-energy boron implants in preamorphized silicon and silicon-on-insulator. <i>Journal of Applied Physics</i> , 2007, 102, 103707.	1.1	9
98	Cellular automaton model of cell response to targeted radiation. <i>Applied Radiation and Isotopes</i> , 2009, 67, 443-446.	0.7	9
99	High-energy heavy ion beam annealing effect on ion beam synthesis of silicon carbide. <i>Surface and Coatings Technology</i> , 2011, 206, 770-774.	2.2	9
100	Hi-C implementation of genome structure for in silico models of radiation-induced DNA damage. <i>PLoS Computational Biology</i> , 2020, 16, e1008476.	1.5	8
101	Nuclear reaction studies of ¹⁵ N implanted spheroidal graphite cast iron using an ion microprobe. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1988, 30, 497-502.	0.6	7
102	Defect production during the fabrication of SOI by oxygen ion implantation. <i>Applied Surface Science</i> , 1989, 36, 400-407.	3.1	7
103	A Monte Carlo study of different LET definitions and calculation parameters for proton beam therapy. <i>Biomedical Physics and Engineering Express</i> , 2022, 8, 015024.	0.6	7
104	Formation mechanisms and structures of insulating compounds formed in silicon by ion beam synthesis. <i>Radiation Effects</i> , 1986, 99, 71-81.	0.4	6
105	Defects in SiO ₂ in buried-oxide structures formed by O ⁺ implantation. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1988, 32, 433-436.	0.6	6
106	Microscope-spectrophotometric analysis to determine the origins of the colour variations on SIMOX wafers. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1991, 55, 718-724.	0.6	6
107	Current/voltage characteristics of ion beam synthesised CoSi ₂ /Si Schottky barrier diodes. <i>Electronics Letters</i> , 1992, 28, 296.	0.5	6
108	Ternary iron-cobalt silicide fabricated by ion beam synthesis. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1995, 96, 356-360.	0.6	6

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109	A Potential Integrated Low Temperature Approach for Superconducting MgB_2 Thin Film Growth and Electronics Device Fabrication by Ion Implantation. IEEE Transactions on Applied Superconductivity, 2005, 15, 3265-3268.	1.1	6
110	Surface proximity and boron concentration effects on end-of-range defect formation during nonmelt laser annealing. Applied Physics Letters, 2008, 92, .	1.5	6
111	Deactivation of submelt laser annealed arsenic ultrashallow junctions in silicon during subsequent thermal treatment. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2010, 28, C1B1-C1B5.	0.6	6
112	The suitability of micronuclei as markers of relative biological effect. Mutagenesis, 2022, 37, 3-12.	1.0	6
113	The location and annealing of paramagnetic oxygen vacancies ($E1'$ centres) in silicon implanted with high doses of oxygen. Journal of Physics Condensed Matter, 1991, 3, 2115-2129.	0.7	5
114	A comparison of shallow and deep iron silicide layers fabricated by ion beam synthesis. Nuclear Instruments & Methods in Physics Research B, 1993, 80-81, 781-785.	0.6	5
115	Micro-PIXE analysis of platinum group minerals from placer deposits. Nuclear Instruments & Methods in Physics Research B, 1993, 77, 444-449.	0.6	5
116	Effects of annealing on doped and undoped ion beam synthesised CoSi_2 structures. Nuclear Instruments & Methods in Physics Research B, 1994, 84, 139-142.	0.6	5
117	On the crystallographic characteristics of ion-beam-synthesized Ru_2Si_3 precipitates. Applied Physics Letters, 2000, 76, 2529-2531.	1.5	5
118	Electrical, electronic and optical characterisation of ion beam synthesised $\hat{\text{I}}^2\text{-FeSi}_2$ light emitting devices. Nuclear Instruments & Methods in Physics Research B, 2001, 175-177, 159-163.	0.6	5
119	Advanced front-end processes for the 45nm CMOS technology node. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2004, 114-115, 118-129.	1.7	5
120	Ion-beam synthesis and photoluminescence of SiC nanocrystals assisted by MeV-heavy-ion-beam annealing. Nuclear Instruments & Methods in Physics Research B, 2012, 282, 88-91.	0.6	5
121	EPR of defects in silicon-on-insulator structures formed by ion implantation. II. N+implantation. Journal of Physics C: Solid State Physics, 1986, 19, 6433-6439.	1.5	4
122	EBIC Study of Silicon on Insulator Structures Formed by High Dose Nitrogen Implantation. Journal of the Electrochemical Society, 1989, 136, 876-878.	1.3	4
123	EPR of defects formed by the implantation into silicon of high doses of carbon. Semiconductor Science and Technology, 1990, 5, 78-82.	1.0	4
124	1990 C R burch prize-joint award. Vacuum, 1991, 42, 1163-1171.	1.6	4
125	Analysis of the structure and defects in heteroepitaxial $\text{Si}/\text{CoSi}_2/\text{Si}$ layers produced by ion beam synthesis and rapid thermal annealing. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1992, 12, 123-127.	1.7	4
126	Non-destructive characterization of thin film SIMOX structures using microscope spectrophotometry. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1992, 12, 185-190.	1.7	4

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127	The properties of $\hat{\Gamma}^2$ -FeSi ₂ fabricated by ion beam assisted deposition as a function of annealing conditions for use in solar cell applications. Nuclear Instruments & Methods in Physics Research B, 2002, 188, 179-182.	0.6	4
128	Effect of buried Si ⁺ SiO ₂ interface on dopant and defect evolution in preamorphizing implant ultrashallow junction. Journal of Vacuum Science & Technology B, 2006, 24, 442.	1.3	4
129	Ion source development and radiobiology applications within the LIBRA project. , 2011, , .		4
130	Automatic cell detection in bright-field microscopy for microbeam irradiation studies. Physics in Medicine and Biology, 2015, 60, 6289-6303.	1.6	4
131	Modifying the current/voltage characteristics of ion beam synthesised CoSi ₂ /Si Schottky barrier diodes by phosphorus and arsenic implantation. Electronics Letters, 1992, 28, 515.	0.5	4
132	A computational approach to quantifying miscounting of radiation-induced double-strand break immunofluorescent foci. Communications Biology, 2022, 5, .	2.0	4
133	Oxygen rich SIMOX?. Semiconductor Science and Technology, 1991, 6, 730-734.	1.0	3
134	Microscope spectrophotometric study of GaAs/Al _x Ga _{1-x} As MBE structures. Journal Physics D: Applied Physics, 1994, 27, 1528-1532.	1.3	3
135	Comparison of boron halide, decaborane and B implants in Si from Molecular Dynamics simulations. Nuclear Instruments & Methods in Physics Research B, 2003, 202, 143-148.	0.6	3
136	Effect of the tilt angle on antimony in silicon implanted wafers. Journal of Applied Physics, 2004, 95, 5471-5474.	1.1	3
137	Comparison of elemental boron and boron halide implants into silicon. Nuclear Instruments & Methods in Physics Research B, 2005, 237, 93-97.	0.6	3
138	Identification and quantitative analysis of calcium phosphate microparticles in intestinal tissue by nuclear microscopy. Nuclear Instruments & Methods in Physics Research B, 2006, 249, 665-669.	0.6	3
139	A microPIXE investigation of the interaction of cells of Schizosaccharomyces pombe with the culture medium. Nuclear Instruments & Methods in Physics Research B, 2007, 260, 231-235.	0.6	3
140	MeV single-ion beam irradiation of mammalian cells using the Surrey vertical nanobeam, compared with broad proton beam and X-ray irradiations. Nuclear Instruments & Methods in Physics Research B, 2013, 307, 586-591.	0.6	3
141	First results on cell irradiation with laser-driven protons on the TARANIS system. , 2013, , .		3
142	Investigating the Intrinsic Noise Limit of Dayem Bridge NanoSQUIDs. IEEE Transactions on Applied Superconductivity, 2014, , 1-1.	1.1	3
143	Automated microbeam observation environment for biological analysis—Custom portable environmental control applied to a vertical microbeam system. Sensors and Actuators B: Chemical, 2017, 239, 1134-1143.	4.0	3
144	Characterizing local dose perturbations due to gas cavities in magnetic resonance—guided radiotherapy. Medical Physics, 2020, 47, 2484-2494.	1.6	3

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145	A preclinical radiotherapy dosimetry audit using a realistic 3D printed murine phantom. Scientific Reports, 2022, 12, 6826.	1.6	3
146	The effect of implantation temperature on defect production in SIMOX structures. Semiconductor Science and Technology, 1989, 4, 626-632.	1.0	2
147	Quantification of the separate matrix constituents of spheroidal graphite cast iron implanted with ^{15}N by nuclear reaction analysis using an ion muprobe. Nuclear Instruments & Methods in Physics Research B, 1992, 64, 452-456.	0.6	2
148	Formation of planar waveguides by implantation of O into cubic silicon carbide. Journal Physics D: Applied Physics, 2001, 34, 257-268.	1.3	2
149	Evaluation of the boron activation and depth distribution using BBr_2^+ implants. , 2002, , .		2
150	Understanding the role of buried Si/SiO ₂ interface on dopant and defect evolution in PAI USJ. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2005, 124-125, 215-218.	1.7	2
151	Deactivation of Ultra Shallow B and BF ₂ Profiles After Non-melt Laser Annealing. Materials Research Society Symposia Proceedings, 2006, 912, 1.	0.1	2
152	PAMELA - a model for an FFAG based hadron therapy machine. , 2007, , .		2
153	Oxygen Depletion in Proton Spot Scanning: A Tool for Exploring the Conditions Needed for FLASH. Radiation, 2021, 1, 290-304.	0.6	2
154	Defects at the Si/SiO ₂ Interface of SiO ₂ Precipitates in Silicon*. Zeitschrift Fur Physikalische Chemie, 1987, 151, 251-257.	1.4	1
155	High energy implantation at the University of Surrey. Nuclear Instruments & Methods in Physics Research B, 1991, 56-57, 630-633.	0.6	1
156	E'1 centres in buried oxide layers formed by oxygen ion implantation into silicon. Nuclear Instruments & Methods in Physics Research B, 1992, 65, 93-96.	0.6	1
157	Segregation of dopants in ion beam synthesised CoSi ₂ layers. Nuclear Instruments & Methods in Physics Research B, 1993, 80-81, 851-856.	0.6	1
158	Interface reaction between Ir films and relaxed SiGe MBE layers by rapid thermal annealing. Journal of Crystal Growth, 1995, 157, 236-241.	0.7	1
159	Recent developments in the use of ion beams at Surrey. Nuclear Instruments & Methods in Physics Research B, 1995, 99, 580-582.	0.6	1
160	Electrical behaviour of arsenic implanted silicon wafers at large tilt angle. , 2002, , .		1
161	Impact-induced desorption of large molecular structures from graphitic substrates. Molecular Simulation, 2005, 31, 95-100.	0.9	1
162	Interaction of the end of range defect band with the upper buried oxide interface for B and BF ₂ implants in Si and silicon on insulator with and without preamorphizing implant. Journal of Vacuum Science & Technology B, 2008, 26, 347.	1.3	1

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163	Influence of the nucleus area distribution on the survival fraction after charged particles broad beam irradiation. <i>Physics in Medicine and Biology</i> , 2014, 59, 4197-4211.	1.6	1
164	Characterisation of Ion Beam Irradiated Zirconolite for Pu Disposition. , 2008, , .		1
165	Simox bibliography. <i>Vacuum</i> , 1991, 42, 393-453.	1.6	0
166	Nuclear microprobe ion-channelling analysis of total dielectric isolation structures in silicon. <i>Semiconductor Science and Technology</i> , 1991, 6, 890-895.	1.0	0
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